

Amendment after Final  
Application No. 10/724,615  
Attorney Docket No. 032152

**AMENDMENTS TO THE CLAIMS**

This listing of claims replaces all prior versions of claims in the application.

**Listing of Claims**

Claims 1-20 (cancelled)

Claim 21 (previously presented): A method for fabricating a ceramic substrate comprising the steps of:

providing a base;

forming a first basic layer, comprising a first layer and a second layer, wherein the first layer is formed by:

screen-printing a first dielectric material in a first region of the base; and

screen-printing a second dielectric material in a second region of the base

other than the first region, the first dielectric material having a dielectric constant different from that of the second dielectric material;

wherein the second layer is formed by screen-printing directly on the first layer;

forming a second basic layer directly on the second layer of the first basic layer, the second basic layer is formed by:

screen-printing a third dielectric material in a third region on the second

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layer, and

screen-printing a fourth dielectric material in a fourth region on the second layer other than the third region;  
releasing the first basic layer from the base; and  
sintering the first basic layer and the second basic layer.

Claim 22 (currently amended): The method for fabricating a ceramic substrate according to claim 23[[21]], wherein a first dielectric layer formed from the first dielectric material has a dielectric constant different from that of a third dielectric layer formed from the third dielectric material.

Claim 23 (previously presented): The method for fabricating a ceramic substrate according to claim 21, further comprising screen-printing a fifth dielectric material in a fifth region of the base at a periphery of the first region, to form a stress mitigating layer.

Claim 24 (previously presented): The method for fabricating a ceramic substrate according to claim 23, wherein the fifth dielectric material comprises at least one component of the first dielectric material and at least one component of the second dielectric material.

Claim 25 (currently amended): The method for fabricating a ceramic substrate according

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to claim 23 [[21]], further comprising screen-printing a conductor paste in a sixth region of the base, to form a via.

Claim 26 (previously presented): The method for fabricating a ceramic substrate according to claim 25, wherein the conductor paste is screen-printed before the second dielectric material is screen-printed.

Claim 27 (previously presented): The method for fabricating a ceramic substrate according to claim 25, wherein further comprising screen-printing a conductor paste on the first basic layer to form a conductor layer.

Claim 28 (previously presented): The method for fabricating a ceramic substrate according to claim 27, further comprising, after the step of forming the conductor layer, pressurizing the first basic layer at the surface where the conductor layer is formed to planarize the surface of the first basic layer, where the conductor layer is formed.

Claim 29 (previously presented): The method for fabricating a ceramic substrate according to claim 27, wherein the conductor layer forms a circuit connected to a first dielectric layer formed from the first dielectric material, the circuit having at least two functions of a transmission interconnection circuit, antenna, a low-pass filter, a high-pass filter, a band-pass

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filter and a capacitor.

Claim 30 (currently amended): The method for fabricating a ceramic substrate according to claim 23[[21]], wherein the second dielectric material is in powder or paste and screen-printed to surround a first dielectric layer formed from the first dielectric material.

Claim 31 (currently amended): The method for fabricating a ceramic substrate according to claim 23[[21]], further forming conductor layers on and below a first dielectric layer formed from the first dielectric material, to form a passive element in the region where the first dielectric layer is formed.